

SWITCHING
N-CHANNEL POWER MOS FET
INDUSTRIAL USE

DESCRIPTION

The 2SK3354 is N-channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

- Super low on-state resistance:
- ★ $R_{DS(on)1} = 8.0 \text{ m}\Omega \text{ MAX. (}V_{GS} = 10 \text{ V, } I_D = 42 \text{ A)}$
- ★ $R_{DS(on)2} = 12 \text{ m}\Omega \text{ MAX. (}V_{GS} = 4 \text{ V, } I_D = 42 \text{ A)}$
- ★ • Low C_{iss} : $C_{iss} = 6300 \text{ pF TYP.}$
- Built-in gate protection diode

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3354	TO-220AB
2SK3354-S	TO-262
2SK3354-Z	TO-220SMD

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage	V_{DSS}	60	V
Gate to Source Voltage	$V_{GSS(AC)}$	± 20	V
Drain Current (DC)	$I_D(DC)$	± 83	A
Drain Current (pulse) ^{Note1}	$I_D(\text{pulse})$	± 332	A
Total Power Dissipation (T _c = 25°C)	P_T	100	W
Total Power Dissipation (T _A = 25°C)	P_T	1.5	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C
★ Single Avalanche Current ^{Note2}	I _{AS}	55	A
★ Single Avalanche Energy ^{Note2}	E _{AS}	302	mJ

Notes 1. PW ≤ 10 μ s, Duty cycle ≤ 1 %

★ 2. Starting T_{ch} = 25 °C, R_G = 25 Ω , V_{GS} = 20 V → 0 V

THERMAL RESISTANCE

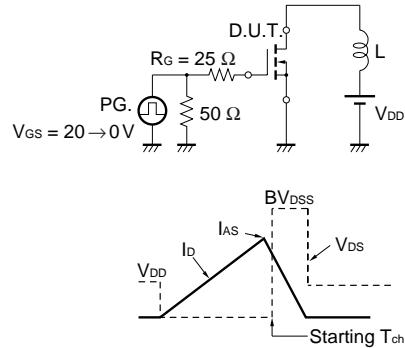
Channel to Case	R _{th(ch-C)}	1.25	°C/W
Channel to Ambient	R _{th(ch-A)}	83.3	°C/W

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 Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

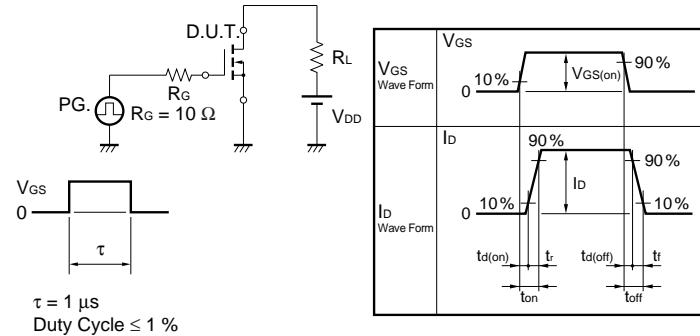
★ ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source On-state Resistance	$R_{DS(on)1}$	$V_{GS} = 10\text{ V}$, $I_D = 42\text{ A}$		6.3	8.0	$\text{m}\Omega$
	$R_{DS(on)2}$	$V_{GS} = 4\text{ V}$, $I_D = 42\text{ A}$		8.0	12	$\text{m}\Omega$
Gate to Source Cut-off Voltage	$V_{GS(\text{off})}$	$V_{DS} = 10\text{ V}$, $I_D = 1\text{ mA}$	1.5	2.0	2.5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = 10\text{ V}$, $I_D = 42\text{ A}$	35	59		S
Drain Leakage Current	I_{DSS}	$V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$			10	μA
Gate to Source Leakage Current	I_{GS}	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0\text{ V}$			± 10	μA
Input Capacitance	C_{iss}	$V_{DS} = 10\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		6300		pF
Output Capacitance	C_{oss}			1000		pF
Reverse Transfer Capacitance	C_{rss}			490		pF
Turn-on Delay Time	$t_{d(on)}$	$I_D = 42\text{ A}$, $V_{GS(\text{on})} = 10\text{ V}$, $V_{DD} = 30\text{ V}$, $R_G = 10\Omega$		100		ns
Rise Time	t_r			1500		ns
Turn-off Delay Time	$t_{d(off)}$			300		ns
Fall Time	t_f			440		ns
Total Gate Charge	Q_G	$I_D = 83\text{ A}$, $V_{DD} = 48\text{ V}$, $V_{GS} = 10\text{ V}$		106		nC
Gate to Source Charge	Q_{GS}			20		nC
Gate to Drain Charge	Q_{GD}			30		nC
Body Diode Forward Voltage	$V_{F(S-D)}$	$I_F = 83\text{ A}$, $V_{GS} = 0\text{ V}$, $di/dt = 100\text{ A}/\mu\text{s}$		1.0		V
Reverse Recovery Time	t_{rr}			55		ns
Reverse Recovery Charge	Q_{rr}			100		nC

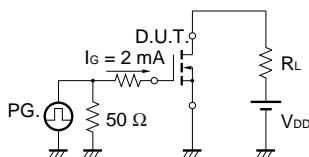
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

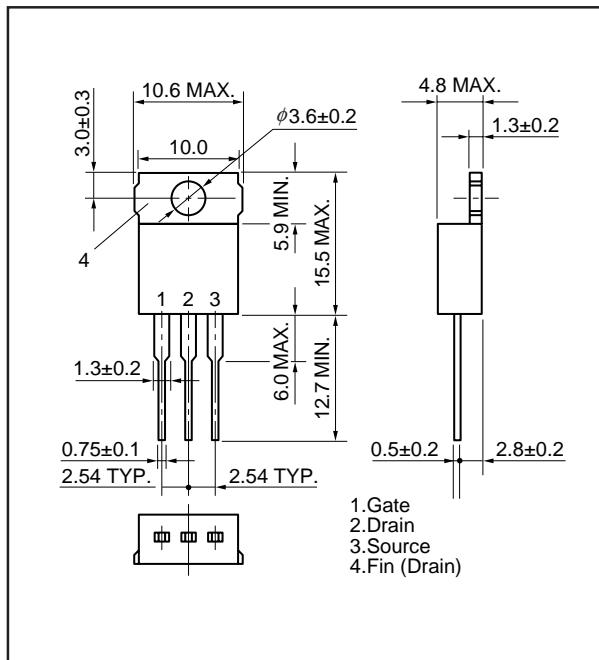


TEST CIRCUIT 3 GATE CHARGE

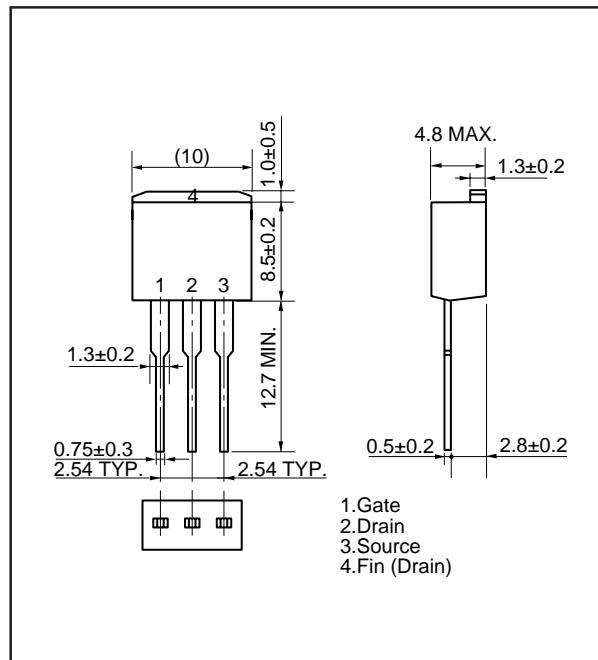


PACKAGE DRAWING (Unit: mm)

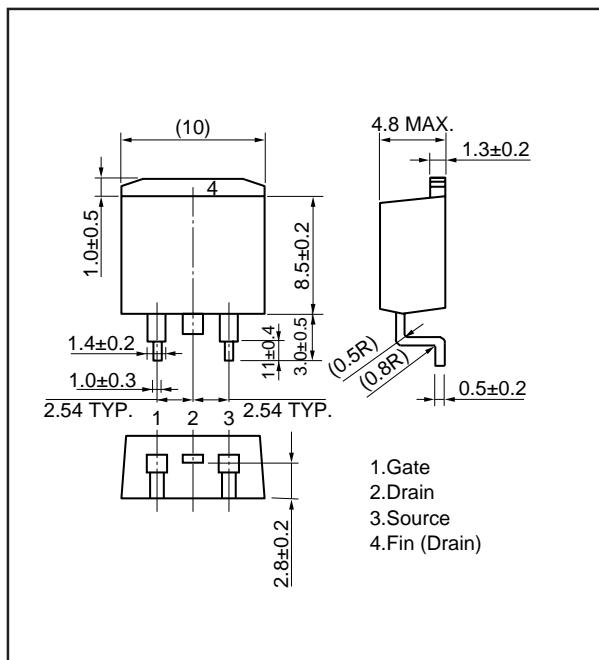
1) TO-220AB (MP-25)



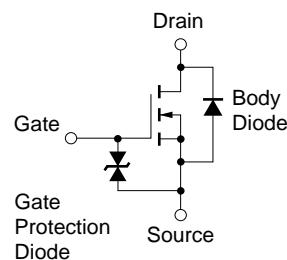
2) TO-262 (MP-25 Fin Cut)



3) TO-220SMD (MP-25Z)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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